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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

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10/28/02  
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OCT 17 2002  
TECHNOLOGY CENTER 2800

IN RE APPLICATION OF: :  
Kenji FUKUDA, et al. : GROUP ART UNIT: 2815  
SERIAL NO.: 09/987,271 :  
FILED: NOVEMBER 14, 2001 : EXAMINER: NGUYEN, J.  
FOR: SiC SEMICONDUCTOR :  
DEVICE

AMENDMENT

ASSISTANT COMMISSIONER FOR PATENTS  
WASHINGTON, D.C. 20231

SIR:

In response to the Office Action dated April 12, 2002, please amend the above-identified application as follows:

IN THE CLAIMS

Please cancel Claims 1 and 17 without prejudice or disclaimer.

Please amend Claims 2 and 8-16 as shown in clean form below:<sup>1</sup>

- Sub  
A' B' →
2. (Amended) A SiC semiconductor device comprising:
- a semiconductor substrate having a P-type silicon carbide region, a gate insulation layer formed on the silicon carbide region;
  - an effective P-type gate electrode formed on the gate insulation layer, an N-type impurity region having an impurity concentration sufficient to form a buried channel region

<sup>1</sup>A marked-up copy of the amendments to the claims is attached hereto.